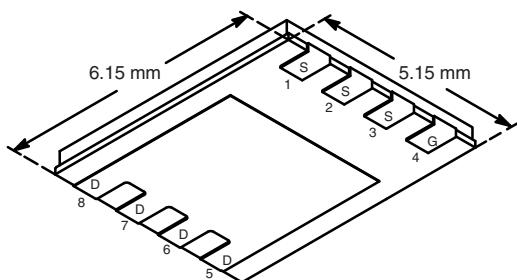


N-Channel 60 V (D-S) Reduced Q_{gd}, Fast Switching MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
60	0.0078 at V _{GS} = 10 V	30	55
	0.009 at V _{GS} = 6 V	30	

PowerPAK SO-8



Bottom View

Ordering Information: Si7138DP-T1-E3 (Lead (Pb)-free)
Si7138DP-T1-GE3 (Lead (Pb)-free) and Halogen-free)

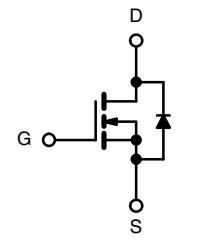
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Low Thermal Resistance PowerPAK® Package
- 100 % R_g and Avalanche Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Primary Side Switch
- Very Low R_g and Q_{gd}, Critical for Minimizing Losses



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	30	A
		30	
		19.7 ^{b, c}	
		15.7 ^{b, c}	
Pulsed Drain Current	I _{DM}	80	
Continuous Source-Drain Diode Current	I _S	30 ^a	A
		4.5 ^{b, c}	
Avalanche Current	I _{AS}	43	
Single-Pulse Avalanche Energy	E _{AS}	93	mJ
Maximum Power Dissipation	P _D	96	W
		61.5	
		5.4 ^{b, c}	
		3.5 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	18	23	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	1.0	1.5	

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile (www.vishay.com/ppg?273461). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 65 °C/W.

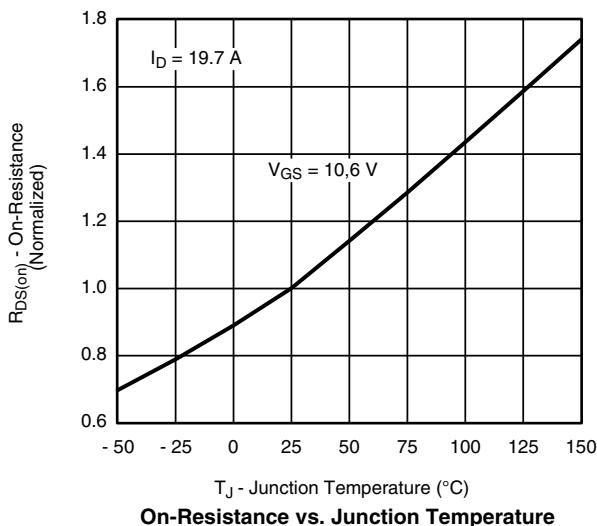
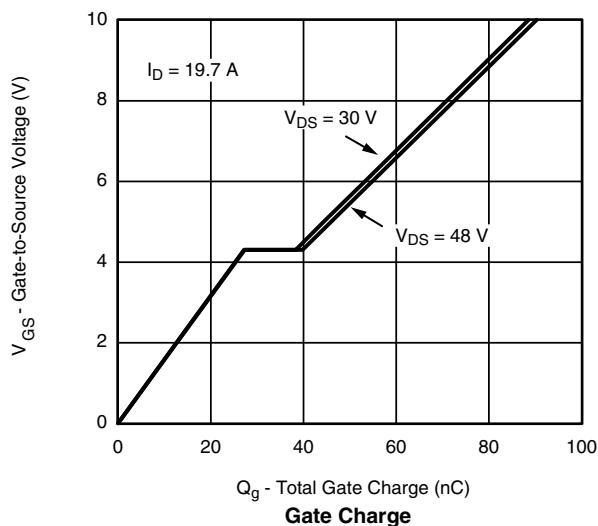
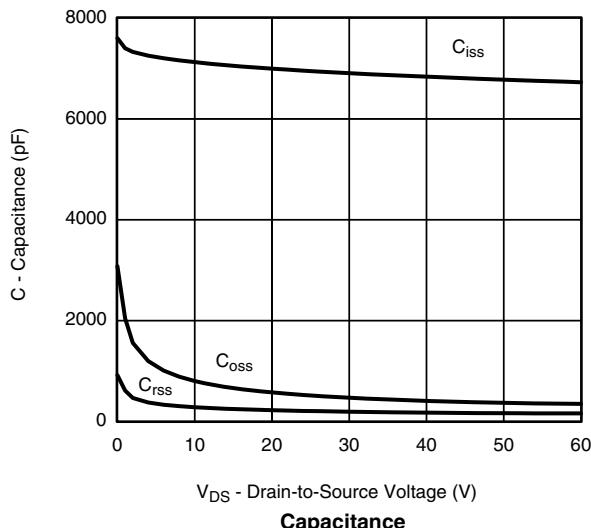
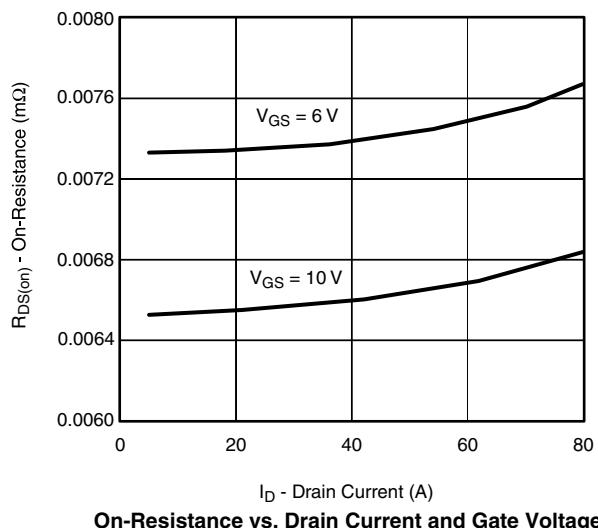
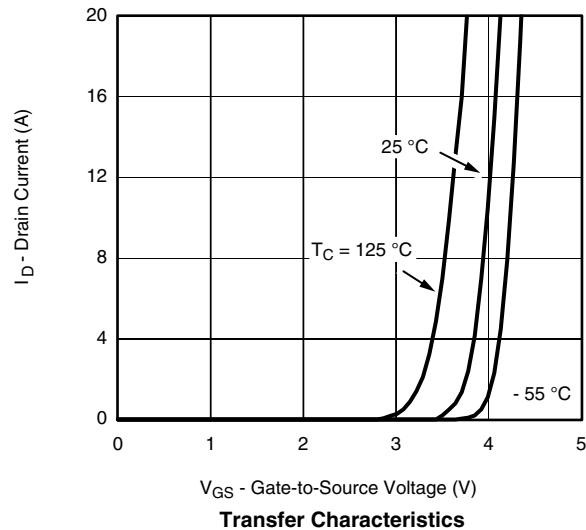
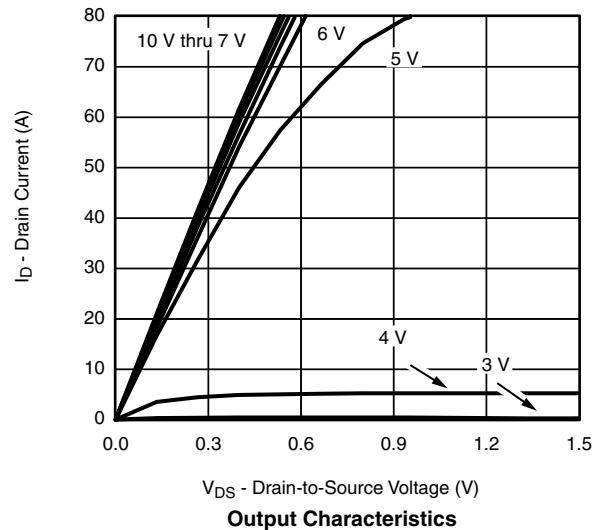
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

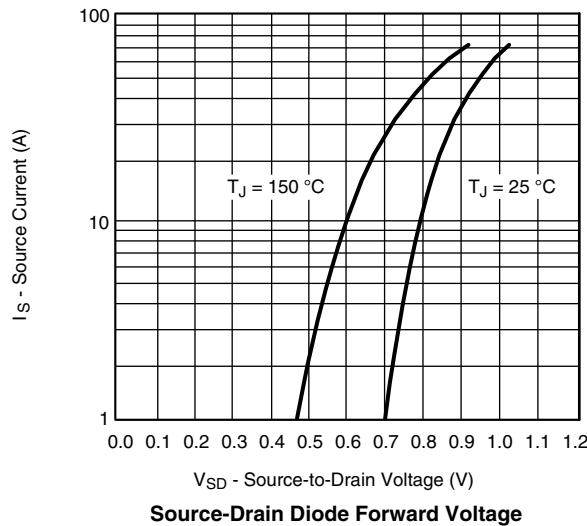
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	60			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		60.5		mV/°C
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			- 8.4		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2		4	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$			1	μA
		$V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 19.7 \text{ A}$		0.0065	0.0078	Ω
		$V_{GS} = 6 \text{ V}$, $I_D = 18 \text{ A}$		0.0073	0.009	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 19.7 \text{ A}$		84		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		6900		pF
Output Capacitance	C_{oss}			470		
Reverse Transfer Capacitance	C_{rss}			200		
Total Gate Charge	Q_g	$V_{DS} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 19.7 \text{ A}$		90	135	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 6 \text{ V}$, $I_D = 19.7 \text{ A}$		55	83	
Gate-Drain Charge	Q_{gd}			27.5		
Gate Resistance	R_g			11		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 30 \text{ V}$, $R_L = 3 \Omega$ $I_D \geq 10 \text{ A}$, $V_{GEN} = 6 \text{ V}$, $R_g = 1 \Omega$		0.6	0.9	Ω
Rise Time	t_r			47	70	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			120	180	
Fall Time	t_f			40	60	
Turn-On Delay Time	$t_{d(\text{on})}$			8	15	
Rise Time	t_r			25	40	
Turn-Off Delay Time	$t_{d(\text{off})}$			12	20	
Fall Time	t_f			50	75	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			30	A
Pulse Diode Forward Current ^a	I_{SM}				80	
Body Diode Voltage	V_{SD}	$I_S = 2.7 \text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		45	70	ns
Body Diode Reverse Recovery Charge	Q_{rr}			80	120	nC
Reverse Recovery Fall Time	t_a			30		ns
Reverse Recovery Rise Time	t_b			15		

Notes:

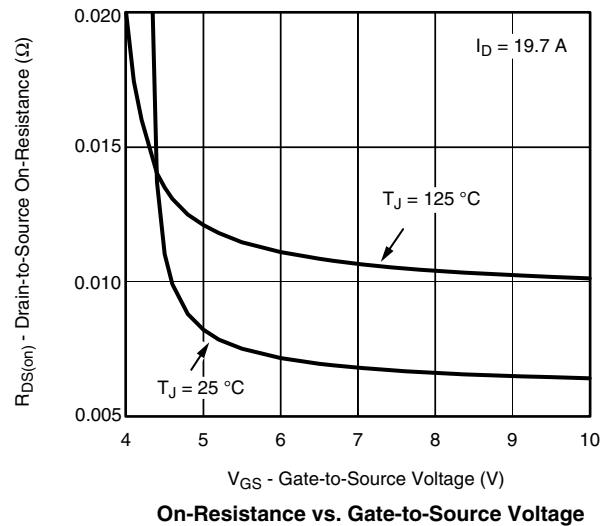
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

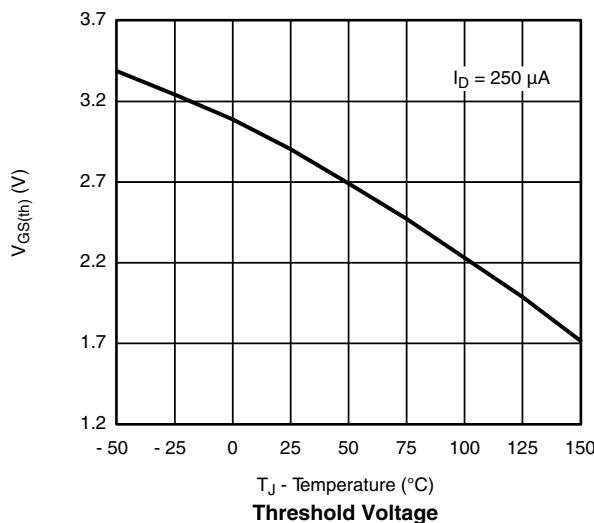
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


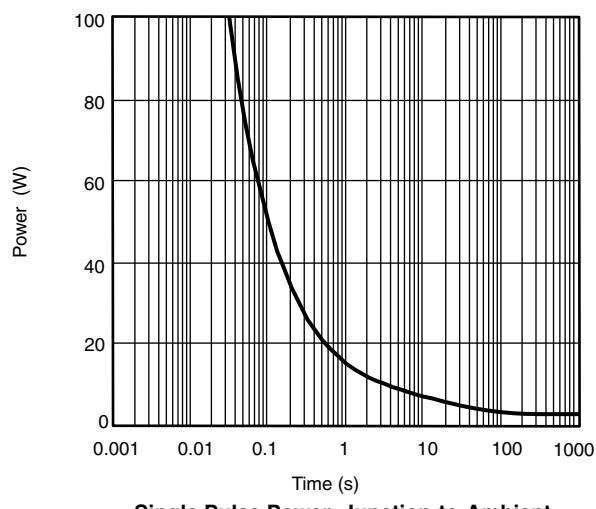
Source-Drain Diode Forward Voltage



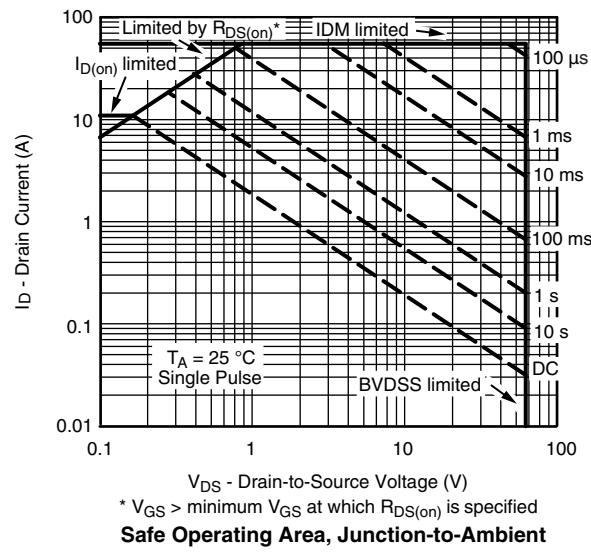
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

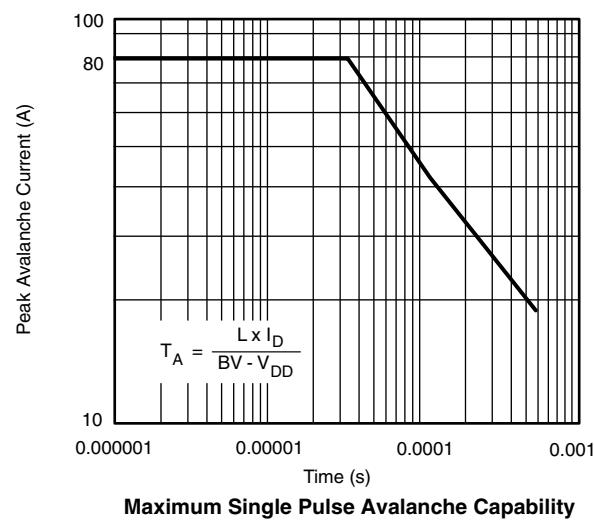
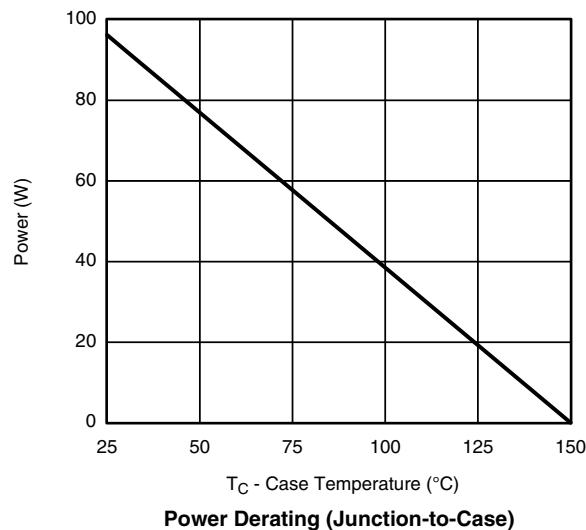
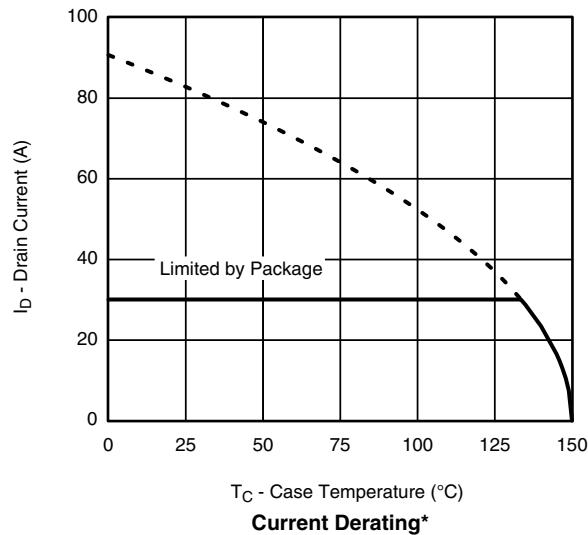


Single Pulse Power, Junction-to-Ambient

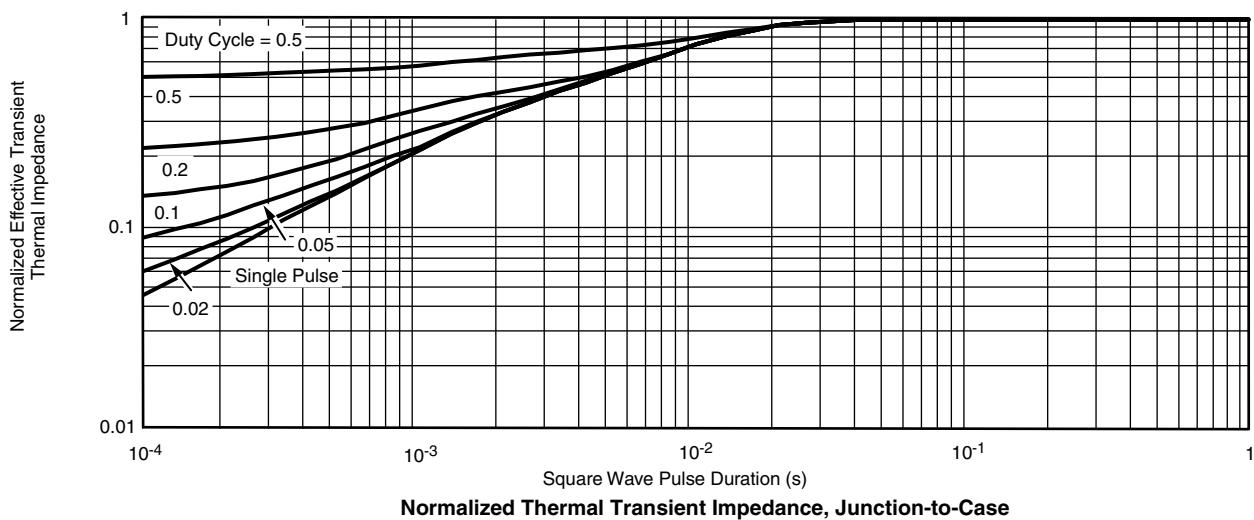
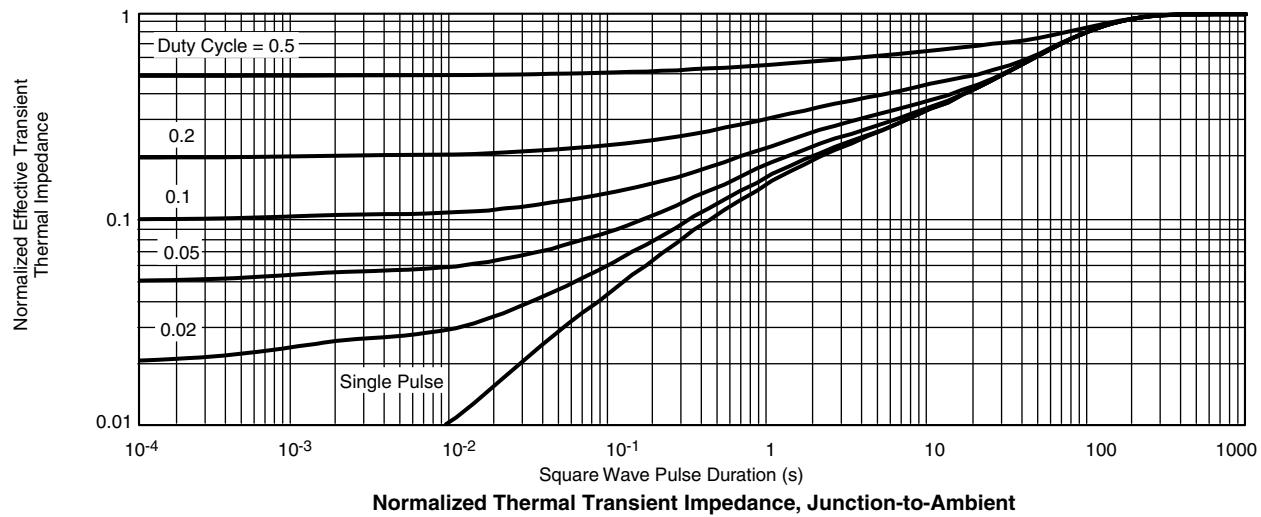


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


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